Inverting Buffer / CMOS Logic Level Shifter with LSTTL-Compatible Inputs

The MC74VHC1GT04 is a single gate inverting buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5.0 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS Logic or from 1.8 V CMOS logic to 3.0 V CMOS Logic while operating at the high-voltage power supply.

The MC74VHC1GT04 input structure provides protection when voltages up to 7.0 V are applied, regardless of the supply voltage. This allows the MC74VHC1GT04 to be used to interface 5.0 V circuits to 3.0 V circuits. The output structures also provide protection when $V_{CC} = 0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

- High Speed: $t_{PD} = 3.8 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 1 \ \mu A$ (Max) at $T_A = 25^{\circ}C$
- TTL–Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- CMOS–Compatible Outputs: $V_{OH} > 0.8 V_{CC}$; $V_{OL} < 0.1 V_{CC}$ @ Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 105; Equivalent Gates = 26
- Pb–Free Package is Available



Figure 1. Pinout (Top View)







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| PIN ASSIGNMENT | | | | | | |
|----------------|-----------------|--|--|--|--|--|
| 1 NC | | | | | | |
| 2 | IN A | | | | | |
| 3 | GND | | | | | |
| 4 | OUT Y | | | | | |
| 5 | V _{CC} | | | | | |

FUNCTION TABLE

| A Input | Y Output |
|---------|------------------|
| L | н |
| Н | L |

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

| Symbol | Chara | cteristics | Value | Unit |
|-----------------------|--------------------------------------|--------------------------------------------------------------------------------------|----------------------------------------------|------|
| V _{CC} | DC Supply Voltage | | -0.5 to +7.0 | V |
| V _{IN} | DC Input Voltage | | -0.5 to +7.0 | V |
| V _{OUT} | DC Output Voltage | V _{CC} = 0 High or Low State | -0.5 to 7.0 -0.5 to V _{CC} + 0.5 | V |
| I _{IK} | Input Diode Current | | -20 | mA |
| I _{OK} | Output Diode Current | V _{OUT} < GND; V _{OUT} > V _{CC} | +20 | mA |
| I _{OUT} | DC Output Current, per Pin | | +25 | mA |
| I _{CC} | DC Supply Current, V_{CC} and GND | | +50 | mA |
| PD | Power dissipation in still air | SC–88A, TSOP–5 | 200 | mW |
| θ_{JA} | Thermal resistance | SC-88A, TSOP-5 | 333 | °C/W |
| TL | Lead temperature, 1 mm from case for | r 10 s | 260 | °C |
| TJ | Junction temperature under bias | | +150 | °C |
| T _{stg} | Storage temperature | | -65 to +150 | °C |
| V _{ESD} | ESD Withstand Voltage | Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3) | > 1500 > 200 N/A | V |
| I _{Latch-Up} | Latch–Up Performance Abo | ve V _{CC} and Below GND at 125°C (Note 4) | ±500 | mA |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Tested to EIA/JESD22-A114-A

2. Tested to EIA/JESD22-A115-A

3. Tested to JESD22-C101-A

4. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

| Symbol | Characteristics | Min | Max | Unit | |
|---------------------------------|-----------------------------|---------------------------------------------------------------------------------------------------------------------------------------------|------------|------------------------|------|
| V _{CC} | DC Supply Voltage | 3.0 | 5.5 | V | |
| V _{IN} | DC Input Voltage | 0.0 | 5.5 | V | |
| V _{OUT} | DC Output Voltage | V _{CC} = 0 High or Low State | 0.0 0.0 | 5.5 V _{CC} | V |
| T _A | Operating Temperature Range | | -55 | +125 | °C |
| t _r , t _f | Input Rise and Fall Time | $\begin{array}{l} {\sf V}_{\rm CC} = 3.3 \; {\sf V} \pm 0.3 \; {\sf V} \\ {\sf V}_{\rm CC} = 5.0 \; {\sf V} \pm 0.5 \; {\sf V} \end{array}$ | 0 0 | 100 20 | ns/V |

Device Junction Temperature versus Time to 0.1% Bond Failures

| Junction Temperature °C | Time, Hours | Time, Years |
|----------------------------|-------------|-------------|
| 80 | 1,032,200 | 117.8 |
| 90 | 419,300 | 47.9 |
| 100 | 178,700 | 20.4 |
| 110 | 79,600 | 9.4 |
| 120 | 37,000 | 4.2 |
| 130 | 17,800 | 2.0 |
| 140 | 8,900 | 1.0 |





| | | | Vcc | ٦ | r _A = 25°0 | C | T _A ≤ | 85°C | $-55 \le T_A$ | ≤ 125°C | |
|------------------|--------------------------------------|------------------------------------------------------------------------------------------|-------------------|-------------------|-----------------------|--------------------|-------------------------|--------------------|-------------------|--------------------|------|
| Symbol | Parameter | Test Conditions | (V) | Min | Тур | Max | Min | Max | Min | Max | Unit |
| V _{IH} | Minimum High-Level Input Voltage | | 3.0 4.5 5.5 | 1.4 2.0 2.0 | | | 1.4 2.0 2.0 | | 1.4 2.0 2.0 | | V |
| V _{IL} | Maximum Low–Level Input Voltage | | 3.0 4.5 5.5 | | | 0.53 0.8 0.8 | | 0.53 0.8 0.8 | | 0.53 0.8 0.8 | V |
| V _{OH} | Minimum High–Level Output Voltage | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \ \mu\text{A}$ | 3.0 4.5 | 2.9 4.4 | 3.0 4.5 | | 2.9 4.4 | | 2.9 4.4 | | V |
| | $V_{IN} = V_{IH} \text{ or } V_{IL}$ | | 3.0 4.5 | 2.58 3.94 | | | 2.48 3.80 | | 2.34 3.66 | | V |
| V _{OL} | Maximum Low-Level Output Voltage | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu\text{A}$ | 3.0 4.5 | | 0.0 0.0 | 0.1 0.1 | | 0.1 0.1 | | 0.1 0.1 | V |
| | $V_{IN} = V_{IH} \text{ or } V_{IL}$ | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4.0 \text{ mA}$ $I_{OL} = 8.0 \text{ mA}$ | 3.0 4.5 | | | 0.36 0.36 | | 0.44 0.44 | | 0.52 0.52 | V |
| I _{IN} | Maximum Input Leakage Current | $V_{IN} = 5.5 \text{ V or GND}$ | 0 to 5.5 | | | ±0.1 | | ±1.0 | | ±1.0 | μΑ |
| I _{CC} | Maximum Quiescent Supply Current | $V_{IN} = V_{CC}$ or GND | 5.5 | | | 1.0 | | 20 | | 40 | μΑ |
| I _{CCT} | Quiescent Supply Current | Input: V _{IN} = 3.4 V | 5.5 | | | 1.35 | | 1.50 | | 1.65 | mA |
| I _{OPD} | Output Leakage Current | V _{OUT} = 5.5 V | 0.0 | | | 0.5 | | 5.0 | | 10 | μΑ |

AC ELECTRICAL CHARACTERISTICS C_{load} = 50 pF, Input t_{r} = t_{f} = 3.0 ns

Power Dissipation Capacitance (Note 5)

C_{PD}

| | | | | T _A = 25°C | | $T_{A} \leq 85^{\circ}C \qquad -55 \leq T_{A} \leq 12$ | | ≤ 125°C | | | |
|----------------------------------------|-------------------------------|----------------------------------|--------------------------------------------------|-----------------------|------------|--------------------------------------------------------|---------|--------------|-------------------------|--------------|------|
| Symbol | Parameter | Test Condit | tions | Min | Тур | Max | Min | Max | Min | Max | Unit |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, | $V_{CC} = 3.3 \pm 0.3 \text{ V}$ | C _L = 15 pF C _L = 50 pF | | 5.0 6.2 | 10.0 13.5 | | 11.0 15.0 | | 13.0 17.5 | ns |
| | Input A to Y | $V_{CC} = 5.0 \pm 0.5 \text{ V}$ | C _L = 15 pF C _L = 50 pF | | 3.8 4.2 | 6.7 7.7 | | 7.5 8.5 | | 8.5 9.5 | |
| C _{IN} | Maximum Input Capacitance | | | | 5.0 | 10 | | 10 | | 10 | pF |
| | | | | | | | Typical | @ 25°C | , V _{CC} = 5.0 |) V | |

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

10

pF





*Includes all probe and jig capacitance

Figure 5. Test Circuit

Figure 4. Switching Waveforms

DEVICE ORDERING INFORMATION

Device Nomenclature Temp Tape & Range Device Circuit Device Package Reel Package Indicator Identifier Function Suffix Order Number Suffix Technology Туре Package[†] 3000 / Tape & Reel MC74VHC1GT04DFT1 MC 74 VHC1G T04 DF T1 SC-88A 178 mm (7 inch) 3000 / Tape & Reel 178 mm (7 inch) VHC1G DF MC74VHC1GT04DFT2 MC 74 T04 T2 SC-88A 3000 / Tape & Reel MC74VHC1GT04DTT1 MC 74 VHC1G T04 DT Τ1 TSOP-5 178 mm (7 inch) SC-88A 3000 / Tape & Reel (Pb-Free) 178 mm (7 inch) MC74VHC1GT04DF2G MC 74 VHC1G T04 DT Τ1

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC-88A-5 / SOT-353 / SC-70-5 DF SUFFIX

CASE 419A-02 ISSUE G







NOTES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 419A-01 OBSOLETE. NEW STANDARD 419A-02.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| | INC | HES | MILLIM | ETERS |
|-----|-------------|-------|----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.071 | 0.087 | 1.80 | 2.20 |
| В | 0.045 | 0.053 | 1.15 | 1.35 |
| С | 0.031 | 0.043 | 0.80 | 1.10 |
| D | 0.004 | 0.012 | 0.10 | 0.30 |
| G | 0.026 | BSC | 0.65 BSC | |
| н | | 0.004 | | 0.10 |
| J | 0.004 | 0.010 | 0.10 | 0.25 |
| Κ | 0.004 0.012 | | 0.10 | 0.30 |
| Ν | 0.008 REF | | 0.20 | REF |
| S | 0.079 | 0.087 | 2.00 | 2.20 |

SOLDERING FOOTPRINT*



SC-88A/SC70-5/SOT-353



PACKAGE DIMENSIONS

TSOP-5 / SOT-23 / SC-59 DT SUFFIX 5-LEAD PACKAGE

CASE 483-02 ISSUE C

В

С

S

⊕ 0.05 (0.002)



- DIES.
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 MAXIMUM LEAD THICKNESS INCLUDES
- CONTROLLING DIMENSION: MILLIMETER.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF PASE MATERIAL
- OF BASE MATERIAL. A AND B DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| | MILLIN | IETERS | INC | HES |
|-----|--------|--------|--------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 2.90 | 3.10 | 0.1142 | 0.1220 |
| В | 1.30 | 1.70 | 0.0512 | 0.0669 |
| С | 0.90 | 1.10 | 0.0354 | 0.0433 |
| D | 0.25 | 0.50 | 0.0098 | 0.0197 |
| G | 0.85 | 1.05 | 0.0335 | 0.0413 |
| н | 0.013 | 0.100 | 0.0005 | 0.0040 |
| J | 0.10 | 0.26 | 0.0040 | 0.0102 |
| K | 0.20 | 0.60 | 0.0079 | 0.0236 |
| L | 1.25 | 1.55 | 0.0493 | 0.0610 |
| М | 0 | 10 | 0 | 10 |
| S | 2.50 | 3.00 | 0.0985 | 0.1181 |

SOLDERING FOOTPRINT*



THIN SOT23-5/TSOP-5/SC59-5

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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